PD - 95495

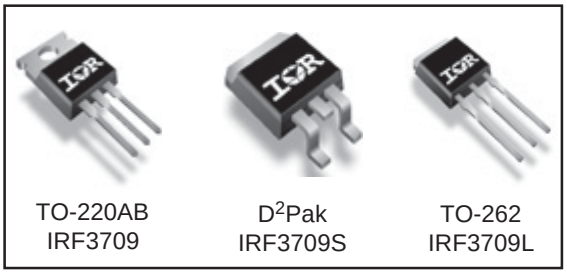
International
IOR Rectifier

SMPS MOSFET

IRF3709PbF
IRF3709SPbF
IRF3709LPBF

HEXFET® Power MOSFET

V_{DSS}	$R_{DS(on)}$ max	I_D
30V	9.0mΩ	90A⑥



TO-220AB
IRF3709

D²Pak
IRF3709S

TO-262
IRF3709L

Applications

- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Server Processor Power Synchronous FET
- Optimized for Synchronous Buck Converters Including Capacitive Induced Turn-on Immunity
- Lead-Free

Benefits

- Ultra-Low Gate Impedance
- Very Low RDS(on) at 4.5V V_{GS}
- Fully Characterized Avalanche Voltage and Current

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	90⑥	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	57	
I_{DM}	Pulsed Drain Current①	360	
P_D @T_C = 25°C	Maximum Power Dissipation③	120	W
P_D @T_A = 25°C	Maximum Power Dissipation⑤	3.1	W
	Linear Derating Factor	0.96	mW/°C
T_J , T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.04	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface ④	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient④	—	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)⑤	—	40	

Notes ① through ⑥ are on page 11

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.029	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	6.4	9.0	mΩ	V_{GS} = 10V, I_D = 15A ③
		—	7.4	10.5		V_{GS} = 4.5V, I_D = 12A ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	3.0	V	V_{DS} = V_{GS}, I_D = 250µA
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	µA	V_{DS} = 24V, V_{GS} = 0V
		—	—	100		V_{DS} = 24V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	V_{GS} = 16V
	Gate-to-Source Reverse Leakage	—	—	-200		V_{GS} = -16V

Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	53	—	—	S	V_{DS} = 15V, I_D = 30A
Q_g	Total Gate Charge	—	27	41	nC	I_D = 15A
Q_{gs}	Gate-to-Source Charge	—	6.7	—		V_{DS} = 16V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	9.7	—		V_{GS} = 5.0V ③
Q_{oss}	Output Gate Charge	—	22	—		V_{GS} = 0V, V_{DS} = 10V
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	V_{DD} = 15V
t_r	Rise Time	—	171	—		I_D = 30A
$t_{d(off)}$	Turn-Off Delay Time	—	21	—		R_G = 1.8Ω
t_f	Fall Time	—	9.2	—		V_{GS} = 4.5V ③
C_{iss}	Input Capacitance	—	2672	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	1064	—		V_{DS} = 16V
C_{rss}	Reverse Transfer Capacitance	—	109	—		f = 1.0MHz

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	382	mJ
I_{AR}	Avalanche Current①	—	30	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	90⑥	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	360		
V_{SD}	Diode Forward Voltage	—	0.88	1.3	V	T_J = 25°C, I_S = 30A, V_{GS} = 0V ③
		—	0.82	—		T_J = 125°C, I_S = 30A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	—	48	72	ns	T_J = 25°C, I_F = 30A, V_R=15V
Q_{rr}	Reverse Recovery Charge	—	46	69	nC	di/dt = 100A/µs ③
t_{rr}	Reverse Recovery Time	—	48	72	ns	T_J = 125°C, I_F = 30A, V_R=15V
Q_{rr}	Reverse Recovery Charge	—	52	78	nC	di/dt = 100A/µs ③

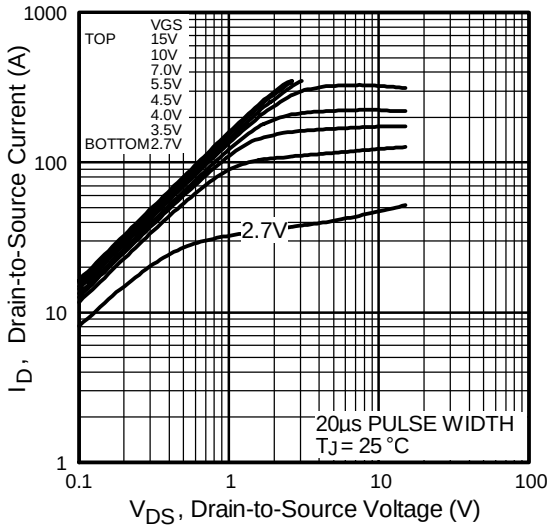


Fig 1. Typical Output Characteristics

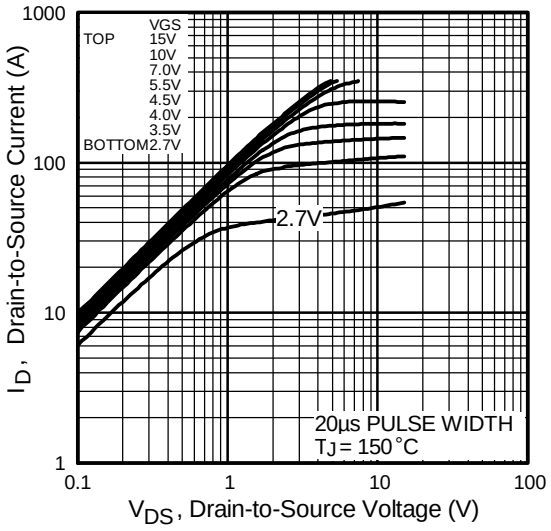


Fig 2. Typical Output Characteristics

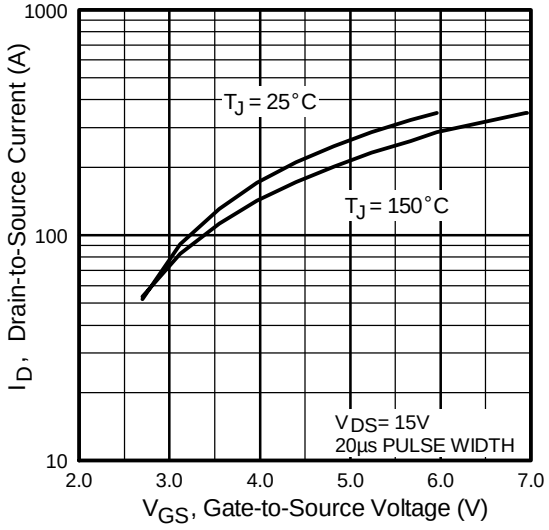


Fig 3. Typical Transfer Characteristics

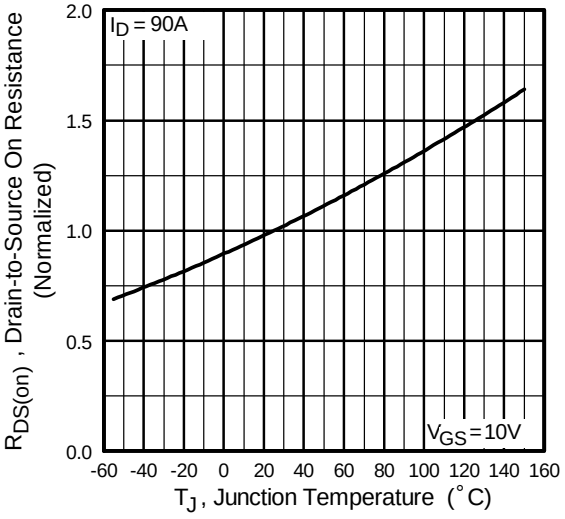


Fig 4. Normalized On-Resistance Vs. Temperature

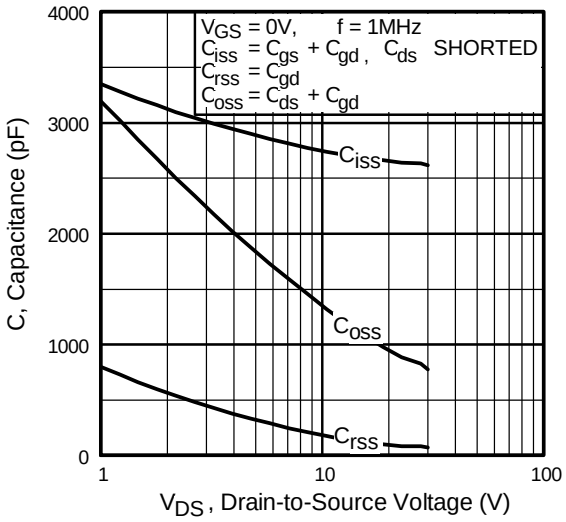


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

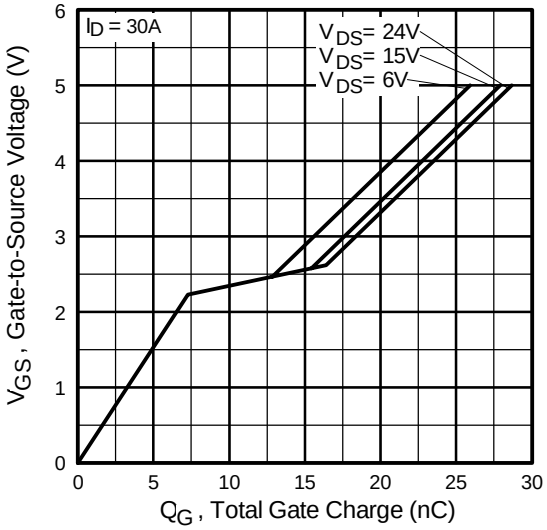


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

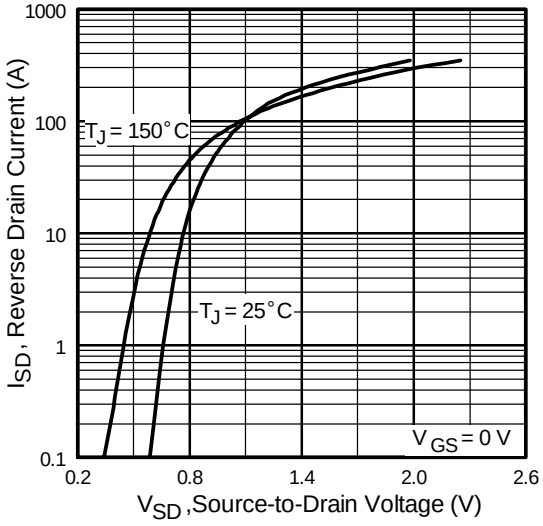


Fig 7. Typical Source-Drain Diode Forward Voltage

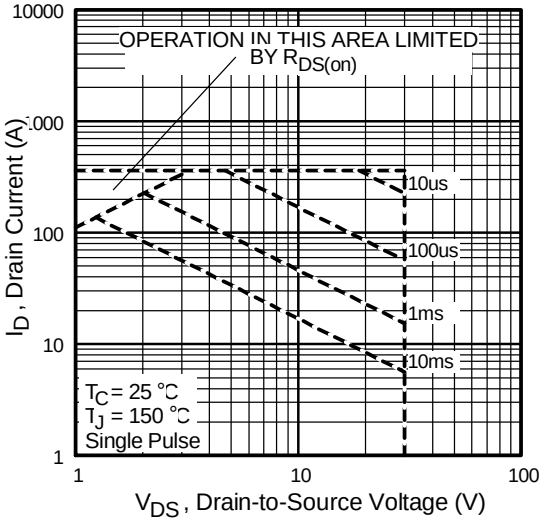


Fig 8. Maximum Safe Operating Area

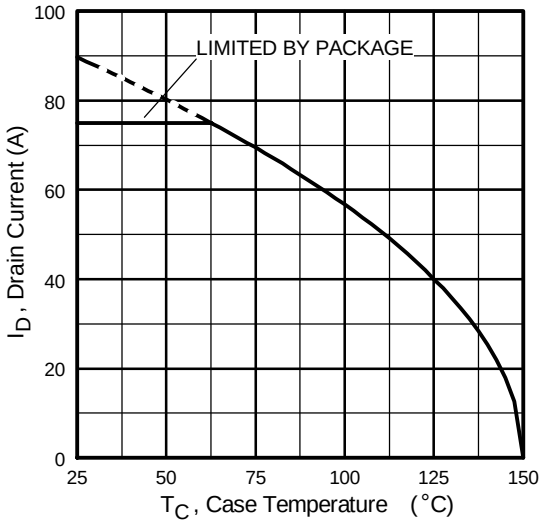


Fig 9. Maximum Drain Current Vs. Case Temperature

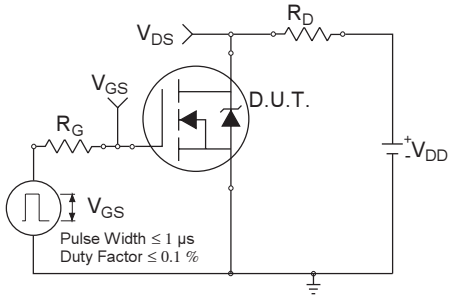


Fig 10a. Switching Time Test Circuit

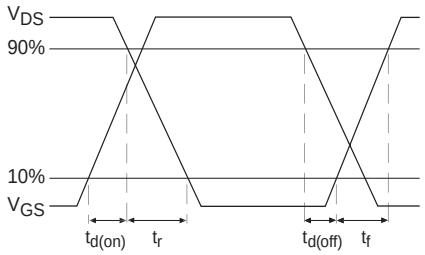


Fig 10b. Switching Time Waveforms

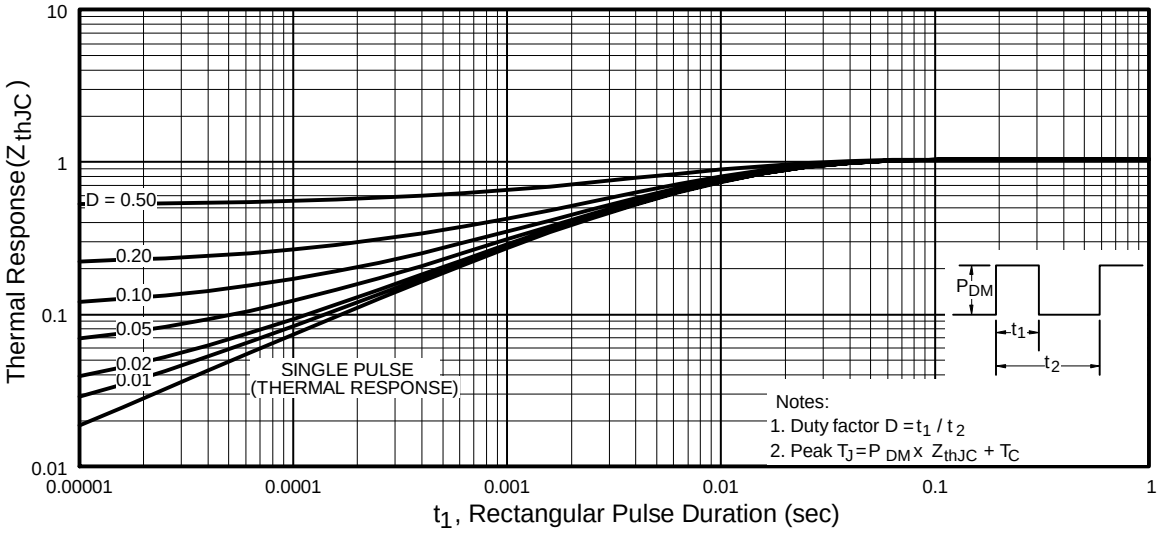


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

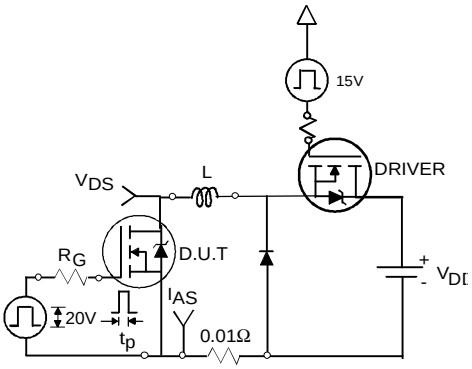


Fig 12a. Unclamped Inductive Test Circuit

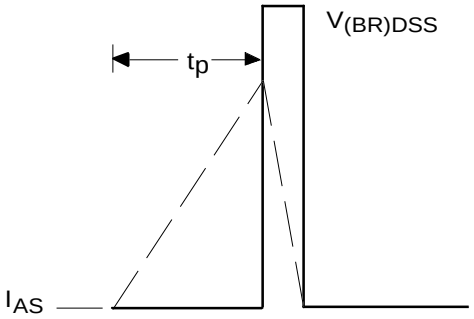


Fig 12b. Unclamped Inductive Waveforms

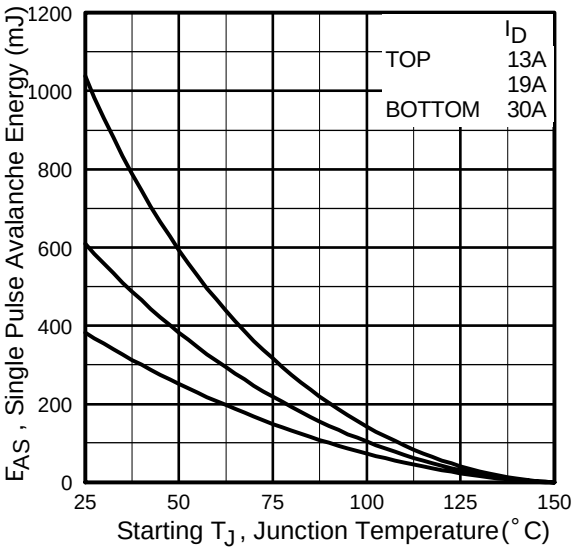


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

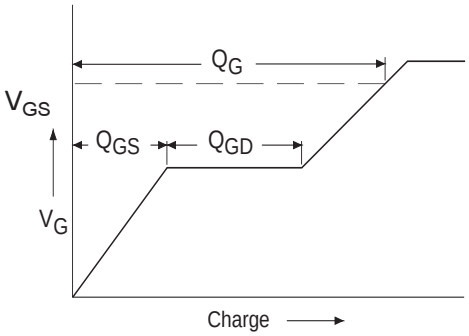


Fig 13a. Basic Gate Charge Waveform

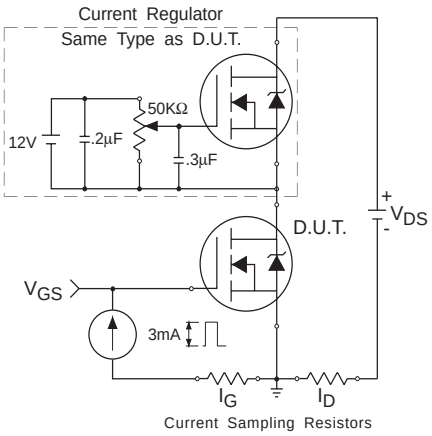


Fig 13b. Gate Charge Test Circuit

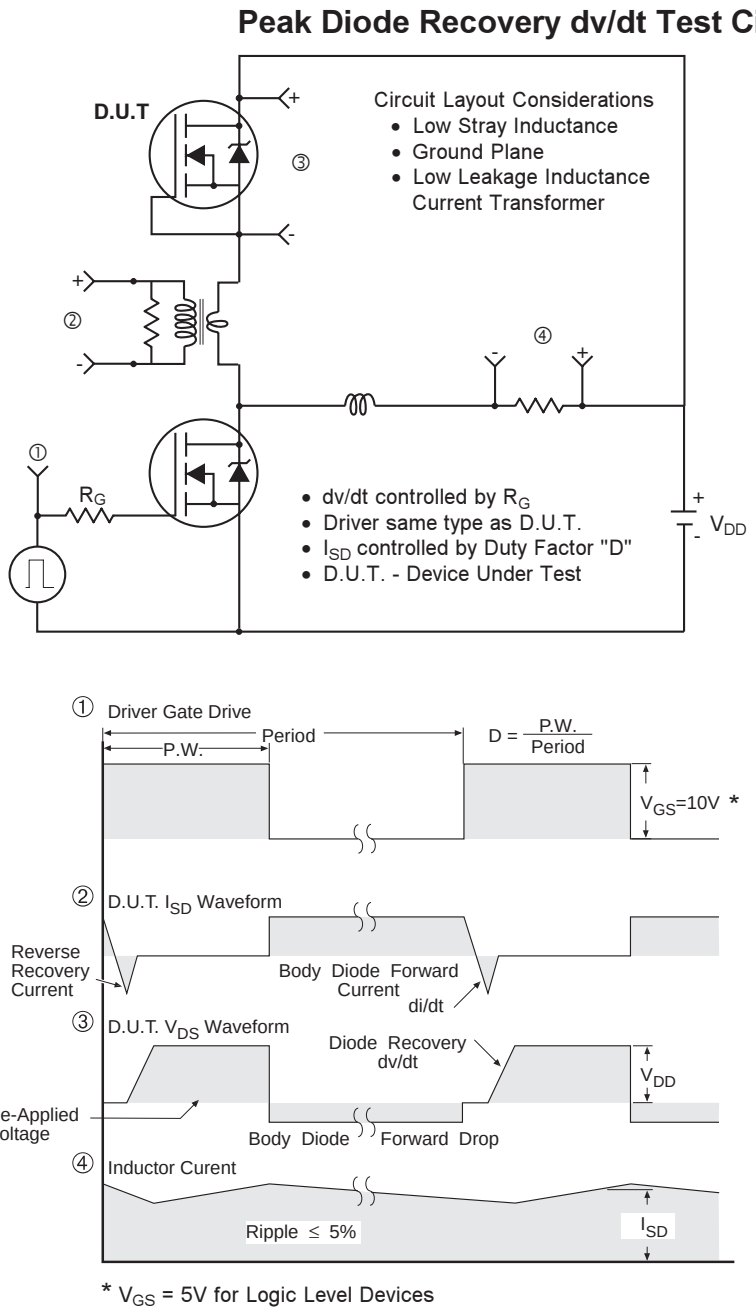
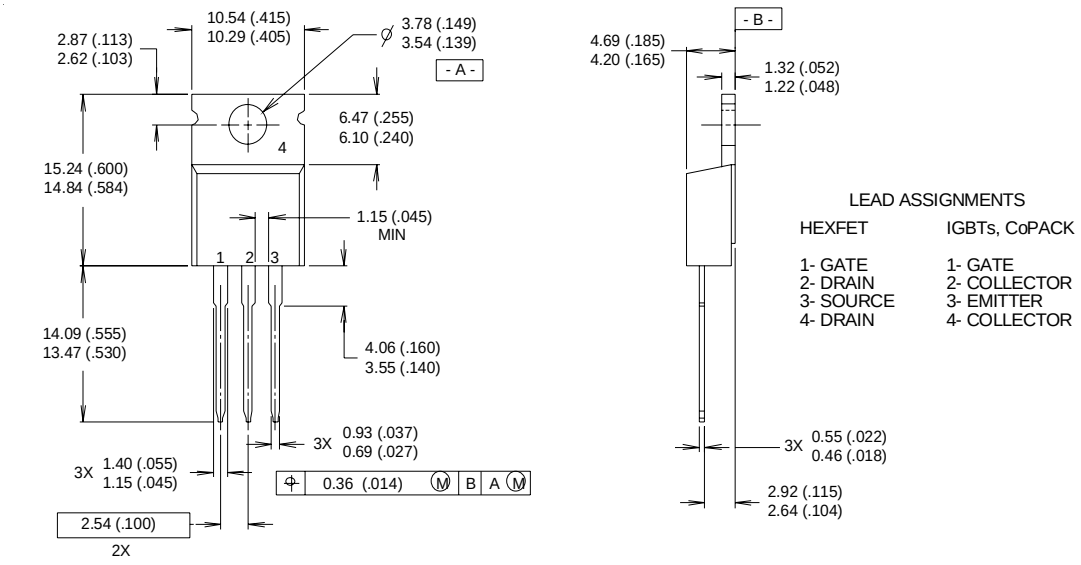


Fig 14. For N-Channel HEXFET® Power MOSFETs

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



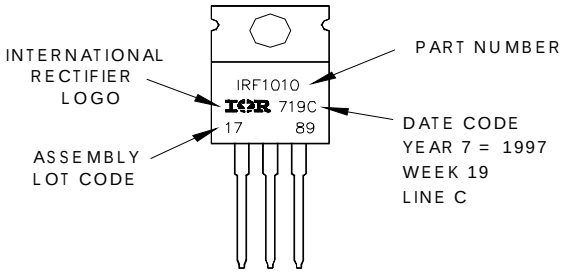
NOTES:

1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
2 CONTROLLING DIMENSION : INCH
3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

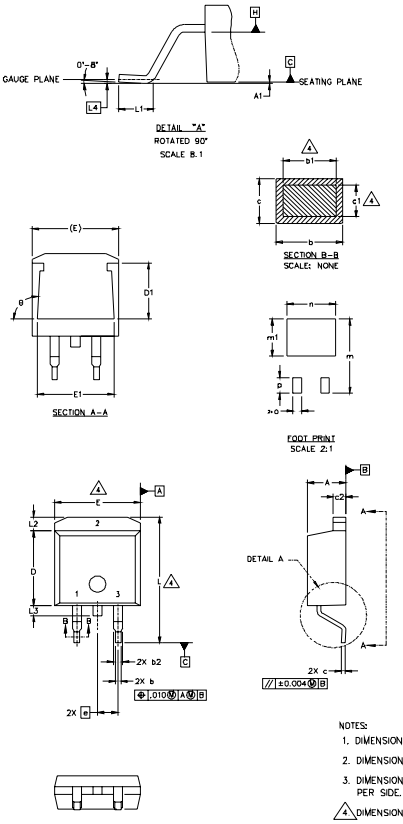
EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"



D²Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	4
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1.– GATE	1.– GATE	1.– ANODE *
2.– DRAIN	2.– COLLECTOR	2.– CATHODE
3.– SOURCE	3.– EMITTER	3.– ANODE

* PART DEPENDENT.

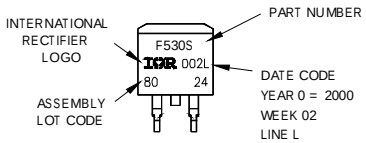
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

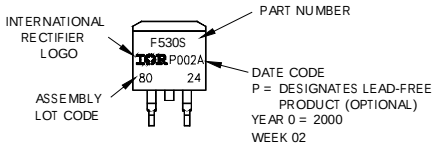
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line
position indicates "Lead-Free"

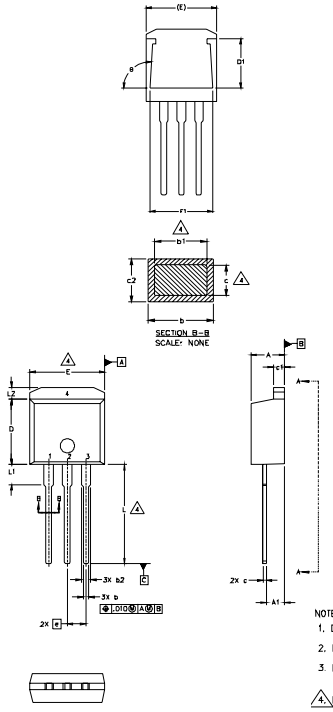


OR



TO-262 Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

LEAD ASSIGNMENTS

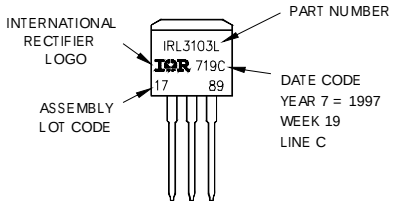
HEXFET	IGBT
1.– GATE	1 – GATE
2.– DRAIN	2 – COLLECTOR
3.– SOURCE	3 – EMITTER
4.– DRAIN	

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"



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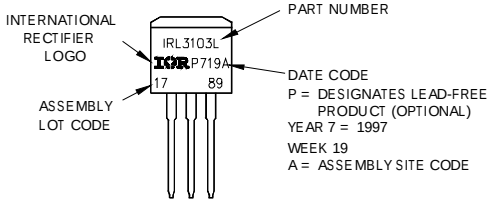
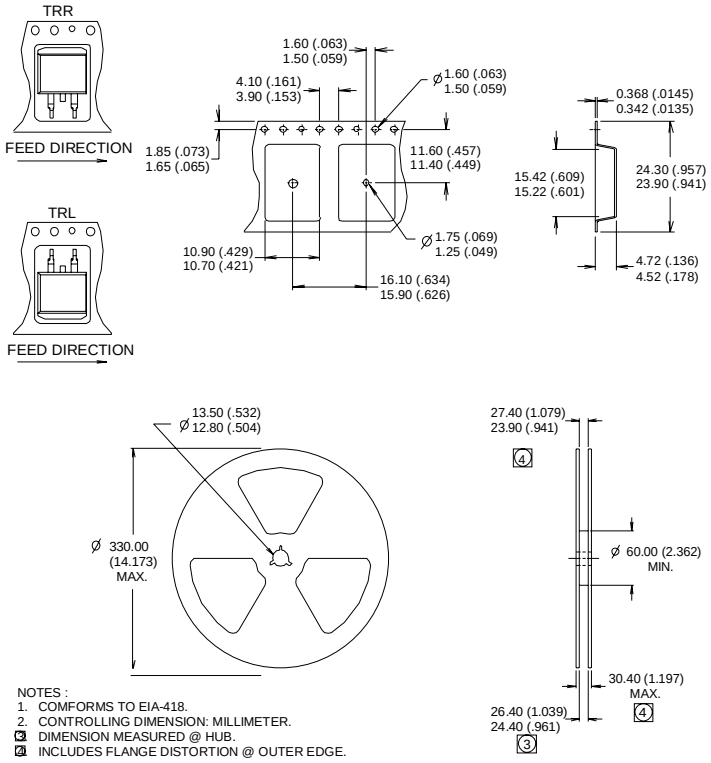


D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :
1. COMFORMS TO EIA-418.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION MEASURED @ HUB.
4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting T_J = 25°C, L = 0.85mH
R_G = 25Ω, I_{AS} = 30A.

③ Pulse width ≤ 400µs; duty cycle ≤ 2%.

④ This is only applied to TO-220AB package

⑤ This is applied to D²Pak, when mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

⑥ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.

Data and specifications subject to change without notice.
This product has been designed and qualified for the industrial market.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information.07/04

Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/